AMERICAN
MICROSEMICONDUCTOR

2N1742 Transistors

Ge PNP Lo-Pwr BJT

Military/High-Rel N

V(BR)CEO (V) 20â

V(BR)CBO (V) 20

I(C) Max. (A) 50m

Absolute Max. Power Diss. (W) 60m

Maximum Operating Temp (øC) 100þ

I(CBO) Max. (A) 10u

@V(CBO) (V) (Test Condition) 10

h(FE) Min. Current gain. 10

h(FE) Max. Current gain.

@I(C) (A) (Test Condition) 2.0m

@V(CE) (V) (Test Condition) 10

h(fe) Min. SS Current gain.

@I(C) (A) (Test Condition)

@V(CE) (V) (Test Condition)

@Freq. (Hz) (Test Condition)

f(T) Min. (Hz) Transition Freq

@I(C) (A) (Test Condition)

@V(CE) (V) (Test Condition)

C(obo) (Max) (F) 1.5p

@V(CB) (V) (Test Condition) 10